The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) An image sensor comprising:

an optical sensor ~~having a first electrode and a second electrode formed over a substrate~~ comprising a gate electrode over a substrate, a polycrystal semiconductor layer formed over said gate electrode with a gate insulating film interposed therebetween, and an amorphous semiconductor layer formed on said polycrystal semiconductor layer;

a thin film transistor electrically connected to ~~a first electrode of~~ said optical sensor in series; and

a capacitor having a first electrode and a second electrode, wherein said first electrode of said capacitor is electrically connected to ~~said first electrode of~~ said optical sensor ~~between said optical sensor~~ and said thin film transistor~~, wherein said second electrode of said capacitor is at a ground potential, and wherein said second electrode of said optical sensor is electrically connected to a bias terminal~~.

2. (Original) An image sensor of claim 1 wherein said image sensor is a linear image sensor.

3. (Previously Presented) An image sensor of claim 1 wherein a gate electrode of said thin film transistor is electrically connected to a shift register circuit.

4. (Previously Presented) An image sensor of claim 1 wherein said thin film transistor is electrically connected to a signal output terminal.

5. (Canceled)

6. (Currently Amended) An image sensor comprising:

an optical sensor ~~having a first electrode and a second electrode formed over a substrate~~ comprising a gate electrode over a substrate, a polycrystal semiconductor layer formed over said gate electrode with a gate insulating film interposed therebetween, and an amorphous semiconductor layer formed on said polycrystal semiconductor layer;

a thin film transistor electrically connected to ~~a first electrode of~~ said optical sensor in series;

D1 a capacitor having a first electrode and a first electrode, wherein said first electrode of said capacitor is electrically connected to ~~said first electrode of~~ said optical sensor ~~between said optical sensor~~ and said thin film transistor~~, wherein said second electrode of said capacitor is at a ground potential, and wherein said second electrode of said optical sensor is electrically connected to a bias terminal~~; and

an amplifier electrically connected to said thin film transistor in series.

2 7. (Original) An image sensor of claim 6 wherein said image sensor is a linear image sensor.

8. (Previously Presented) An image sensor of claim 6 wherein a gate electrode of said thin film transistor is electrically connected to at least one shift register circuit.

9. (Previously Presented) An image sensor of claim 6 wherein said amplifier is electrically connected to a signal output terminal.

10.-55. (Canceled)

56. (Currently Amended) An image sensor comprising:

an optical sensor ~~having a first electrode and a second electrode formed over a substrate~~ comprising a gate electrode over a substrate, a polycrystal semiconductor layer formed over said gate electrode with a gate insulating film interposed therebetween, and an amorphous semiconductor layer formed on said polycrystal semiconductor layer;

a thin film transistor electrically connected to ~~a first electrode of~~ said optical sensor; and

a capacitor having a first electrode and a second electrode, wherein said first electrode of said capacitor is electrically connected to ~~said first electrode of~~ said optical sensor ~~between said optical sensor~~ and said thin film transistor~~, wherein said second electrode of said capacitor is at a ground potential, and wherein said second electrode of said optical sensor is electrically connected to a bias terminal~~.

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2 57. (Previously Presented) An image sensor of claim 56 wherein said image sensor is a linear image sensor.

3 58. (Previously Presented) An image sensor of claim 56 wherein a gate electrode of said thin film transistor is electrically connected to a shift register circuit.

4 59. (Previously Presented) An image sensor of claim 56 wherein said thin film transistor is electrically connected to a signal output terminal.

60. (Currently Amended) An image sensor comprising:

an optical sensor ~~having a first electrode and a second electrode formed over a substrate~~ comprising a gate electrode over a substrate, a polycrystal semiconductor layer formed over said gate electrode with a gate insulating film interposed

therebetween, and an amorphous semiconductor layer formed on said polycrystal semiconductor layer;

a thin film transistor electrically connected to ~~a first electrode of~~ said optical sensor;

a capacitor having a first electrode and a first electrode, wherein said first electrode of said capacitor is electrically connected to ~~said first electrode of~~ said optical sensor ~~between said optical sensor~~ and said thin film transistor~~, wherein said second electrode of said capacitor is at a ground potential, and wherein said second electrode of said optical sensor is electrically connected to a bias terminal~~; and

an amplifier electrically connected to said thin film transistor in series.

61. (Previously Presented) An image sensor of claim 60 wherein said image sensor is a linear image sensor.

62. (Previously Presented) An image sensor of claim 60 wherein a gate electrode of said thin film transistor is electrically connected to at least one shift register circuit.

63. (Previously Presented) An image sensor of claim 60 wherein said amplifier is electrically connected to a signal output terminal.

64. (New) An image sensor comprising:

an optical sensor comprising a gate electrode over a substrate, a polycrystal semiconductor layer formed over said gate electrode with a gate insulating film interposed therebetween, and an amorphous semiconductor layer formed on said polycrystal semiconductor layer; and

a thin film transistor electrically connected to said optical sensor.

2 65. (New) An image sensor of claim 64 wherein said image sensor is a linear image sensor.

3 66. (New) An image sensor of claim 64 wherein a gate electrode of said thin film transistor is electrically connected to a shift register circuit.

4 67. (New) An image sensor of claim 64 wherein said thin film transistor is electrically connected to a signal output terminal.

68. (New) An image sensor comprising:

an optical sensor comprising a gate electrode over a substrate, a polycrystal semiconductor layer formed over said gate electrode with a gate insulating film interposed therebetween, and an amorphous semiconductor layer formed on said polycrystal semiconductor layer;

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a thin film transistor electrically connected to said optical sensor; and

an amplifier electrically connected to said thin film transistor in series.

69. (New) An image sensor of claim 68 wherein said image sensor is a linear image sensor.

70. (New) An image sensor of claim 68 wherein a gate electrode of said thin film transistor is electrically connected to at least one shift register circuit.

71. (New) An image sensor of claim 68 wherein said amplifier is electrically connected to a signal output terminal.